

AllnGaP LED DICE

Part NO.: AOC-S14OxM-65 Series

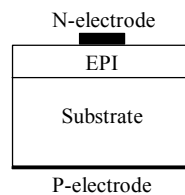
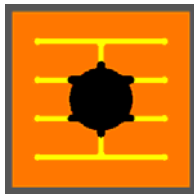
Features

- Orange color emission
- Excellent performance and high efficiency
- Great reliability even in harsh environment
- Mirror reflector to increase efficiency

Description

AOC-S14OxM-65 series is a orange color emitting AllnGaP LED grown by MOCVD technique. Its structure enables enhanced quantum efficiency; the mirror reflector greatly increases the light extraction efficiency and therefore a greater light intensity. This device is designed for ultrahigh brightness (UHB) automobile, display, and consumer electronic applications.

Chip Dimensions



Chip Size : 355 μ m \times 355 μ m \pm 25 μ m
 Bonding Pad : ϕ 100 μ m \pm 10 μ m
 Chip Thickness : 165 μ m \pm 25 μ m

Electrical and Optics Characteristics

Measuring Item	Symbol	Condition	Min	Typ.	Max	Unit
Forward Voltage	V _F	I _F =20mA	1.75	-	2.30	V
Reverse Current	I _R	V _R =5V	-	-	1.0	μ A
Dominant Wavelength	λ_d	I _F =20mA	600	-	620	nm
Max. Junction Temperature	T _{max}	-	\leq 120			$^{\circ}$ C
Max. DC forward current	I _F	T _a = 25 $^{\circ}$ C	\leq 70			mA
Max. pulse forward current (Pulse width 0.1 msec, frequency=1 kHz.)	I _{fm}	T _a = 25 $^{\circ}$ C	\leq 140			mA
Storage temperature	T _{stg}	Chip on tape	0 ~ 40			$^{\circ}$ C
		Only chip	-40 ~ 80			

Available Dominate Wavelength and Iv Matrix

Part No.	Wavelength Range	\geq 520 mcd	\geq 600 mcd	\geq 700 mcd	\geq 800 mcd
S14OSM-65	600 ~ 610 nm	-	Y60	Y70	Y80
S14OLM-65	610 ~ 620 nm	Y52	Y60	Y70	-

Note:

1. All measurements are done with AOC's standard testing equipment.
2. Luminance intensity is measured on bare chip.
3. Above contents are subject to change without notice.
4. Special requests are also welcome, please contact AOC's sale representative for any request.
5. Characteristics curves are measured within TO-46 package.

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